BGA7127 400 MHz to 2700 MHz 0.5 W high linearity silicon amplifier Rev. 3 – 3 December 2010 Product data sheet

1. Product profile

1.1 General description

The MMIC is a one-stage amplifier, offered in a low-cost leadless surface-mount package. It delivers 28 dBm output power at 1 dB gain compression and a superior performance up to 2700 MHz. Its power saving features include simple quiescent current adjustment, which allows class-AB operation and logic-level shutdown control to reduce the supply current to 4 μ A.

1.2 Features and benefits

- 400 MHz to 2700 MHz frequency operating range
- 12 dB small signal gain at 2 GHz
- 28 dBm output power at 1 dB gain compression
- Integrated active biasing
- External matching allows broad application optimization of the electrical performance
- 5 V single supply operation
- All pins ESD protected

1.3 Applications

- Broadband CPE/MoCA
- WLAN/ISM/RFID
- Wireless infrastructure (base station, repeater, backhaul systems)
- Industrial applications
- E-metering
- Satellite Master Antenna TV (SMATV)

1.4 Quick reference data

Table 1. Quick reference data

Input and output impedances matched to 50 Ω , SHDN = HIGH (shutdown disabled). Typical values at V_{CC} = 5 V; I_{CC} = 180 mA; T_{case} = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f	frequency		[1]	400	-	2700	MHz
Gp	power gain	f = 2140 MHz		10.5	12.0	13.5	dB
P _{L(1dB)}	output power at 1 dB gain compression	f = 2140 MHz		26.5	28.0	-	dBm
IP3 ₀	output third-order intercept point	f = 2140 MHz	[2]	39.0	42.0	-	dBm

[1] Operation outside this range is possible but not guaranteed.

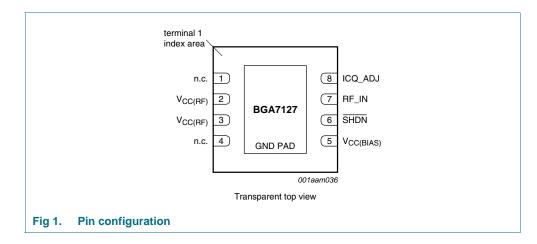
[2] $P_L = 17 \text{ dBm per tone}$; spacing = 1 MHz.



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2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2.	Pin description	
Symbol	Pin	Description
n.c.	1, 4	not connected
$V_{CC(RF)}$	2, 3	RF output for the power amplifier and DC supply input for the RF transistor collector $\begin{bmatrix} 1 \end{bmatrix}$
V _{CC(BIAS)}	5	bias supply voltage [2]
SHDN	6	shutdown control function enabled / disabled
RF_IN	7	RF input for the power amplifier [1]
ICQ_ADJ	8	quiescent collector current adjustment by an external resistor
GND	GND pad	RF ground and DC ground 3

[1] This pin is DC-coupled and requires an external DC-blocking capacitor.

[2] RF decoupled.

[3] The center metal base of the SOT908-1 also functions as heatsink for the power amplifier.

3. Ordering information

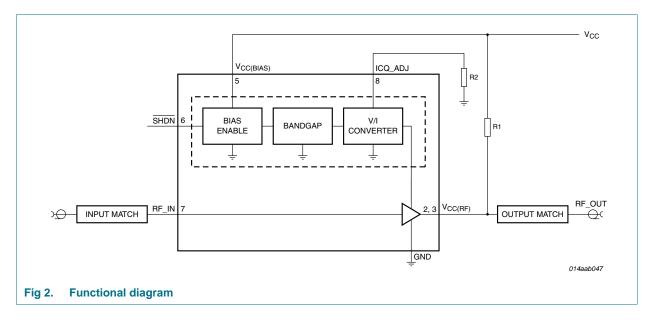
Table 3. Ordering information

Type number	er Package						
	Name	Description	Version				
BGA7127	HVSON8	plastic thermal enhanced very thin small outline package; no leads; 8 terminals; body $3 \times 3 \times 0.85$ mm	SOT908-1				

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4. Functional diagram



5. Shutdown control

Table 4.Shutdown control settings

Mode	Mode description	Function descriptionSHDNVctrl(sd) (V)Ictrl		Function description SHDN V _{ctrl(sd)} (V)		V _{ctrl(sd)} (V)		I _{ctrl(sd)} (μ Α)
				Min	Max	Min	Max		
Idle	medium power MMIC fully off; minimal supply current	shutdown control enabled	0	0	0.7	-	2		
ТΧ	medium power MMIC transmit mode	shutdown control disabled	1	2.5	V _{CC(BIAS)}	-	3		

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6. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

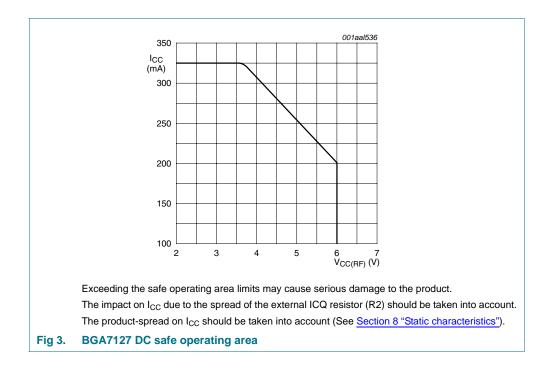
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC(RF)}	RF supply voltage		<u>[1]</u>	-	6.0	V
V _{CC(BIAS)}	bias supply voltage		<u>[1]</u>	-	6.0	V
I _{CC}	supply current		[1][2]	-	325	mA
V _{ctrl(sd)}	shutdown control voltage		[3]	0.0	V _{CC(BIAS)}	V
P _{i(RF)}	RF input power	f = 2140 MHz; switched	<u>[4]</u>	-	25	dBm
T _{case}	case temperature			-40	+85	°C
Tj	junction temperature			-	150	°C
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E		-	2000	V
		Charged Device Model (CDM); According JEDEC standard 22-C101B		-	500	V

[1] See Figure 3 for safe operating area.

[2] The supply current is adjustable. See Section 8.1 "Supply current adjustment" and Section 12 "Application information".

[3] If V_{ctrl(sd)} exceeds V_{CC(BIAS)}, the internal ESD circuit can be damaged. The recommended preventive measure is to limit the I_{ctrl(sd)} to 20 mA. If the SHDN function is not used, the SHDN pin should be connected to V_{CC(BIAS)}.

[4] Withstands switching between zero and maximum P_{i(RF)}.



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7. Thermal characteristics

Table 6.	Thermal characteristics				
Symbol	Parameter	Conditions	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	$T_{case} = 85 \ ^{\circ}C; V_{CC} = 5 \ V;$ $I_{CC} = 180 \ mA$	[<u>1]</u> 28	-	K/W

[1] Defined as thermal resistance from junction to GND pad.

8. Static characteristics

Table 7. Static characteristics

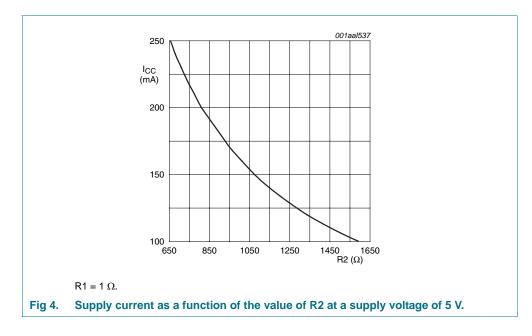
Input and output impedances matched to 50 Ω , $\overline{SHDN} = HIGH$ (shutdown disabled). Typical values at V_{CC} = 5.0 V; T_{case} = 25 °C; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current		[<u>1]</u> 100	-	250	mA
		R1 = 1 Ω; R2 = 909 Ω, E96	^[2] 160	180	200	mA
		R1 = 1.8 Ω; R2 = 909 Ω, E96	^[2] 160	180	200	mA
		during shutdown; pin SHDN = LOW (shutdown enabled)	-	4	6	μA

- [1] The supply current is adjustable. See <u>Section 8.1 "Supply current adjustment"</u> and <u>Section 12 "Application</u> information".
- [2] See Section 12 "Application information".

8.1 Supply current adjustment

The supply current can be adjusted by changing the value of external ICQ resistor (R2).



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9. Dynamic characteristics

Table 8. Dynamic characteristics

Input and output impedances matched to 50 Ω , SHDN = HIGH (shutdown disabled). Typical values at V_{CC} = 5 V; I_{CC} = 180 mA; T_{case} = 25 °C; see Section 12 "Application information"; unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	frequency		<u>[1]</u> 400	-	2700	MHz
G _p	power gain	f = 940 MHz	[2] _	20.0	-	dB
		f = 1960 MHz	[2] _	13.0	-	dB
		f = 2140 MHz	2 10.5	12.0	13.5	dB
		f = 2445 MHz	[2] _	10.5	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	f = 940 MHz	-	27.5	-	dBm
		f = 1960 MHz	-	28.5	-	dBm
		f = 2140 MHz	26.5	28.0	-	dBm
		f = 2445 MHz	-	27.5	-	dBm
IP3 ₀	output third-order intercept point	f = 940 MHz	<u>[3]</u>	41.5	-	dBm
		f = 1960 MHz	<u>[3]</u>	42.5	-	dBm
		f = 2140 MHz	<u>3</u> 39.0	42.0	-	dBm
		f = 2445 MHz	<u>[3]</u>	41.5	-	dBm
NF	noise figure	f = 940 MHz	-	3.1	-	dB
		f = 1960 MHz	-	4.5	-	dB
		f = 2140 MHz	-	4.6	-	dB
		f = 2445 MHz	-	4.7	-	dB
RL _{in}	input return loss	f = 940 MHz	[2] _	-25	-	dB
		f = 1960 MHz	[2] _	-9	-	dB
		f = 2140 MHz	[2] _	-9	-	dB
		f = 2445 MHz	[2] _	-11	-	dB
RL _{out}	output return loss	f = 940 MHz	[2] _	-12	-	dB
		f = 1960 MHz	[2] _	-14	-	dB
		f = 2140 MHz	[2] _	-10	-	dB
		f = 2445 MHz	[2]	-17	-	dB

[1] Operation outside this range is possible but not guaranteed.

[2] Defined at $P_i = -40$ dBm; small signal conditions.

[3] $P_L = 17$ dBm; tone spacing = 1 MHz.

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9.1 Scattering parameters

Table 9. Scattering parameters, MMIC only

 $V_{CC} = 5 V; I_{CC} = 180 mA; T_{case} = 25 °C.$

f (MHz)	S ₁₁		s ₂₁		S ₁₂		\$ ₂₂		
	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	Magnitude (ratio)	Angle (degree)	
400	0.92	178	8.64	91	0.01	45	0.75	–173	
500	0.91	176	6.95	88	0.01	49	0.76	-175	
600	0.91	174	5.88	86	0.01	51	0.75	-176	
700	0.91	172	5.05	83	0.02	53	0.75	-178	
800	0.91	170	4.47	81	0.02	55	0.74	-180	
900	0.91	167	4.01	79	0.02	55	0.74	179	
1000	0.90	165	3.64	76	0.02	54	0.75	177	
1100	0.90	163	3.30	74	0.02	52	0.76	175	
1200	0.90	161	3.0	71	0.02	51	0.75	173	
1300	0.91	159	2.75	69	0.03	50	0.76	172	
1400	0.91	156	2.53	67	0.03	51	0.76	171	
1500	0.92	155	2.33	65	0.03	52	0.77	170	
1600	0.92	153	2.16	64	0.03	52	0.77	169	
1700	0.92	152	2.01	62	0.03	51	0.78	168	
1800	0.92	152	1.86	61	0.03	48	0.78	168	
1900	0.93	151	1.75	60	0.03	49	0.79	168	
2000	0.93	152	1.64	60	0.03	51	0.80	168	
2100	0.93	151	1.56	59	0.04	52	0.80	169	
2200	0.93	151	1.48	58	0.04	52	0.80	169	
2300	0.92	151	1.43	57	0.04	52	0.80	170	
2400	0.92	151	1.38	57	0.04	52	0.79	171	
2500	0.90	152	1.33	57	0.04	51	0.80	172	
2600	0.90	152	1.29	56	0.04	50	0.79	173	
2700	0.89	152	1.27	55	0.05	50	0.78	173	

10. Reliability information

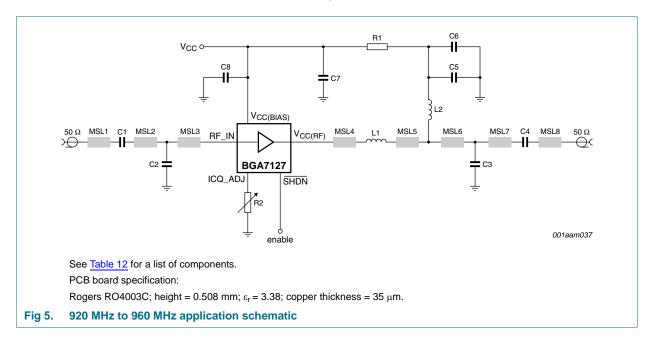
Table 10.	Reliability	
Life test	Conditions	Intrinsic failure rate
HTOL	according to JESD85; confidence level 60 %; $T_j = 55$ °C; activation energy = 0.7 eV; acceleration factor determined according to the Arrhenius equation.	4

11. Moisture sensitivity

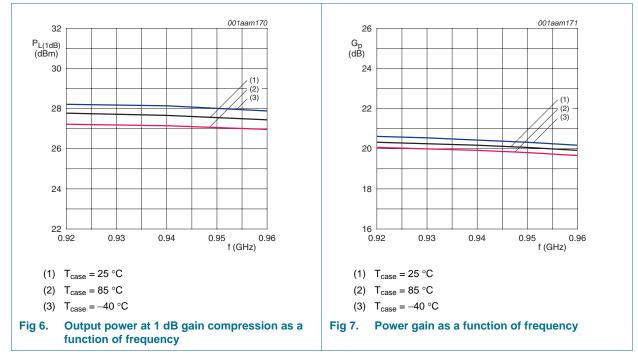
	Table 11. Moisture sensitivity level	
	Test methodology	Class
	JESD-22-A113	1
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12. Application information

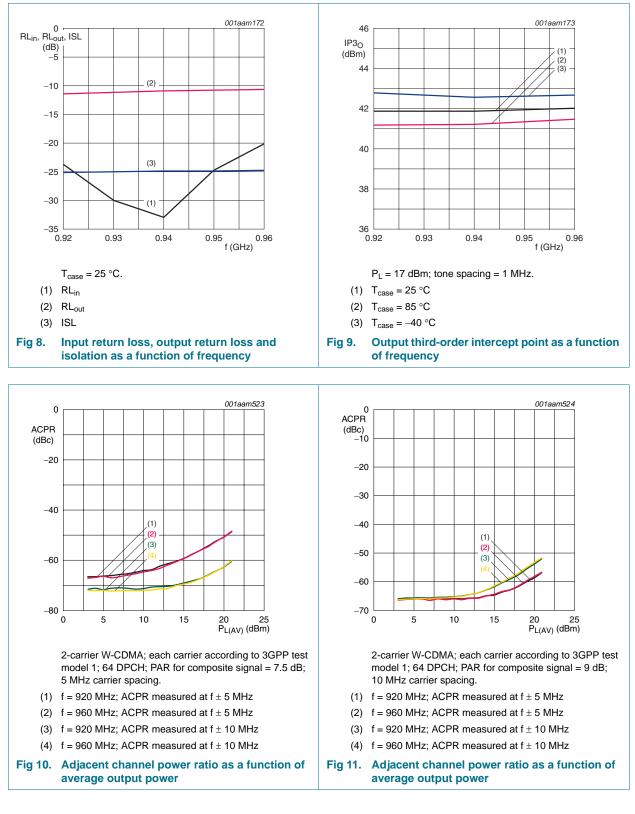






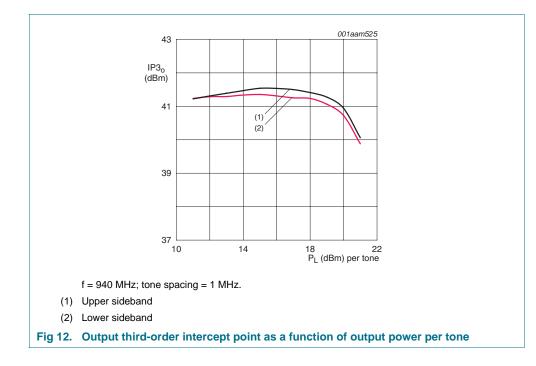
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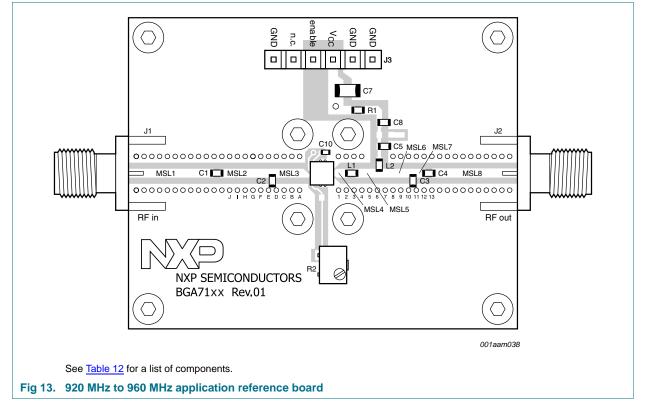
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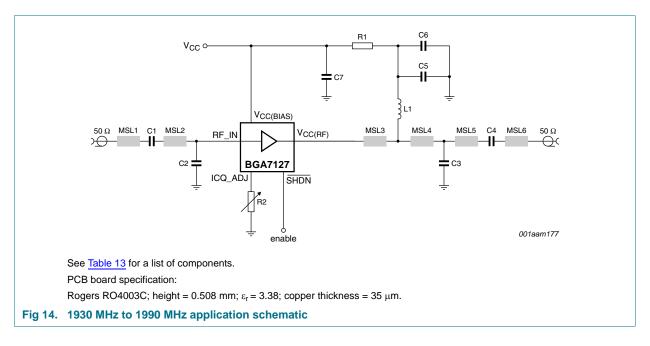
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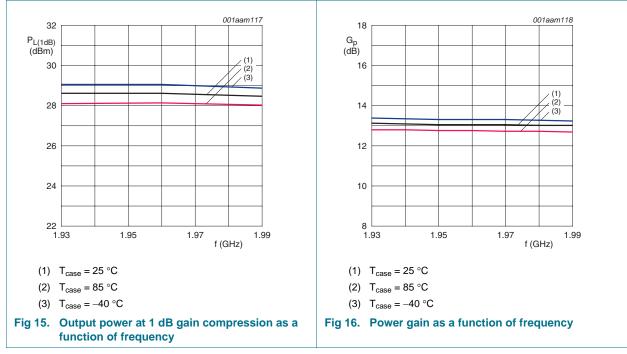
Component	Description	Value	Function	Remarks
C1, C4	capacitor	68 pF	DC blocking	GRM1885C1H680JA01D
C2	capacitor	9.1 pF	input match	Murata GRM1885C1H9R1CZ01D
C3	capacitor	5.1 pF	output match	Murata GRM1885C1H5R1CZ01D
C5	capacitor	10 nF	RF decoupling	Murata GRM1885C1H1R0CZ01D
C6	capacitor	1 μF	LF decoupling	AVX 06033D105KAT2A
C7	capacitor	10 μF	LF decoupling	AVX 1206ZG106ZAT2A
C8	capacitor	12 pF	noise decoupling	Murata GRM1555C1H120JZ01D
J1, J2	RF connector	SMA		Emerson Network Power 142-0701-841
J3	DC connector	6 pins		MOLEX
L1	inductor	2.2 nH	output match	Tyco Electronics 36501J2N2JTDG
L2	inductor	22 nH	DC Feed	Tyco Electronics 36501J022JTDG
	PCB	RO4003C stack		KOVO
MSL1	micro stripline	1.14 mm \times 0.8 mm \times 10.95 mm	input match	Width (W) \times Spacing (S) \times Length (L)
MSL2	micro stripline	1.14 mm \times 0.8 mm \times 6.8 mm	input match	Width (W) \times Spacing (S) \times Length (L)
MSL3	micro stripline	1.14 mm \times 0.8 mm \times 4.4 mm	input match	Width (W) \times Spacing (S) \times Length (L)
MSL4	micro stripline	1.14 mm \times 0.8 mm \times 2.0 mm	output match	Width (W) \times Spacing (S) \times Length (L)
MSL5	micro stripline	1.14 mm \times 0.8 mm \times 3.2 mm	output match	Width (W) \times Spacing (S) \times Length (L)
MSL6	micro stripline	1.14 mm \times 0.8 mm \times 4.2 mm	output match	Width (W) \times Spacing (S) \times Length (L)
MSL7	micro stripline	1.14 mm \times 0.8 mm \times 1.8 mm	output match	Width (W) \times Spacing (S) \times Length (L)
MSL8	micro stripline	1.14 mm \times 0.8 mm \times 10.95 mm	output match	Width (W) \times Spacing (S) \times Length (L)
R1	resistor	1.8 Ω		Yageo RC0603FR-071R8L
R2	resistor	2 k Ω trimmer	bias adjustment	Bourns 3214W-1-202E

Table 12.920 MHz to 960 MHz list of componentsSee Figure 5 and Figure 13 for component layout.

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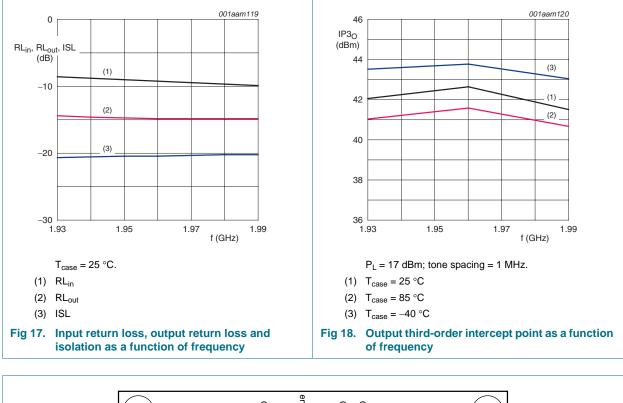


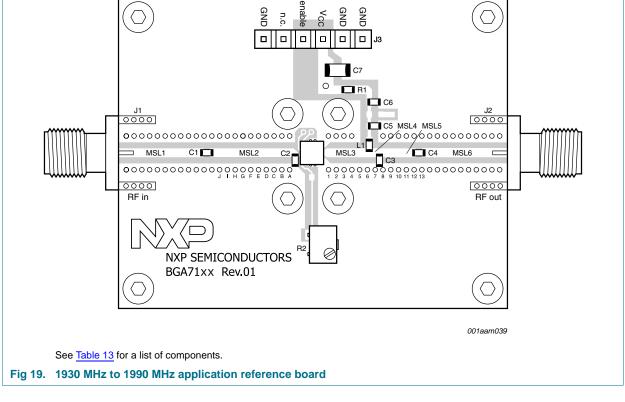




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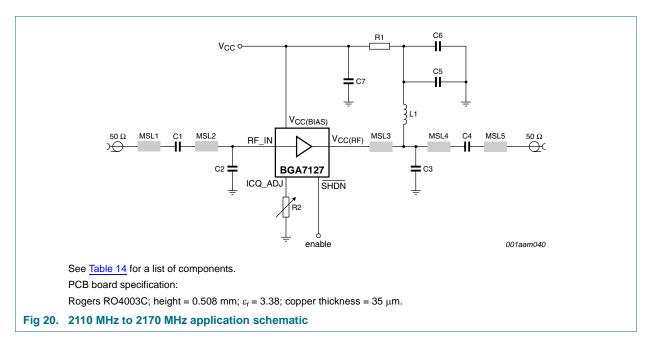
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Printed-Circuit Board (PCB): Rogers RO4003C stack; height = 0.508 mm; copper plating thickness = 35 µm. **Component Description** Value Function Remarks C1,C4 DC blocking GRM1885C1H150JA01D capacitor 15 pF C2 capacitor 2.7 pF input match Murata, GRM1885C1H2R7CZ01D C3 capacitor 1.8 pF output match Murata, GRM1885C1H1R8CZ01D C5 capacitor 15 pF RF decoupling Murata, GRM1885C1H150JA01D C6 capacitor 100 nF LF decoupling AVX, 0603YC104KAT2A C7 capacitor 10 μF LF decoupling AVX, 1206ZG106ZAT2A J1,J2 RF connector SMA Emerson Network Power, 142-0701-841 J3 DC connector 6 pins MOLEX L1 inductor 22 nH DC Feed Tyco Electronics, 36501J022JTDG MSL1 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 10.95 \text{ mm}$ input match Width (W) \times Spacing (S) \times Length (L) MSL2 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 11.4 \text{ mm}$ input match Width (W) \times Spacing (S) \times Length (L) MSL3 $1.14 \text{ mm} \times 0.8 \text{ mm} \times 5.9 \text{ mm}$ micro stripline output match Width (W) \times Spacing (S) \times Length (L) MSL4 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 1.4 \text{ mm}$ output match Width (W) \times Spacing (S) \times Length (L) MSL5 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 4.6 \text{ mm}$ output match Width (W) \times Spacing (S) \times Length (L) MSL6 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 10.95 \text{ mm}$ output match Width (W) \times Spacing (S) \times Length (L) R1 resistor 1Ω Yageo, RC0603FR-071RL R2 resistor 2 kΩ trimmer bias adjustment Bourns, 3214W-1-202E

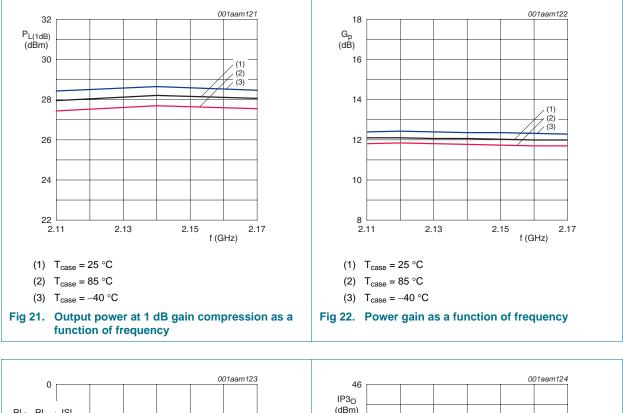
Table 13. 1930 MHz to 1990 MHz list of components See Figure 14 and Figure 19 for component layout.

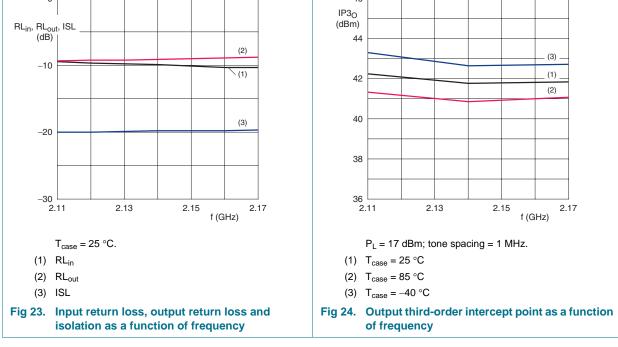
12.3 2110 MHz to 2170 MHz at 5 V; 180 mA



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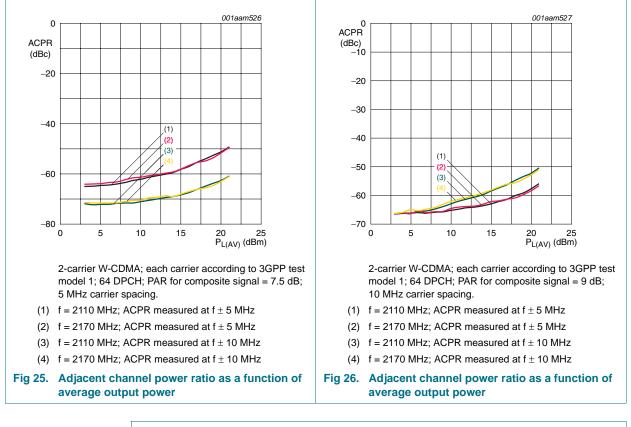


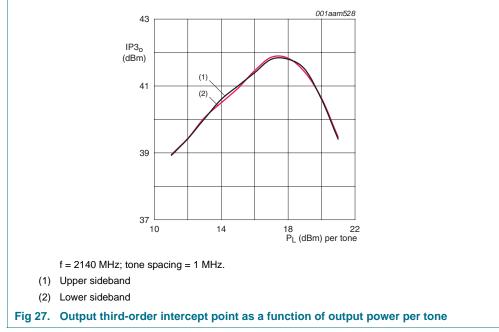


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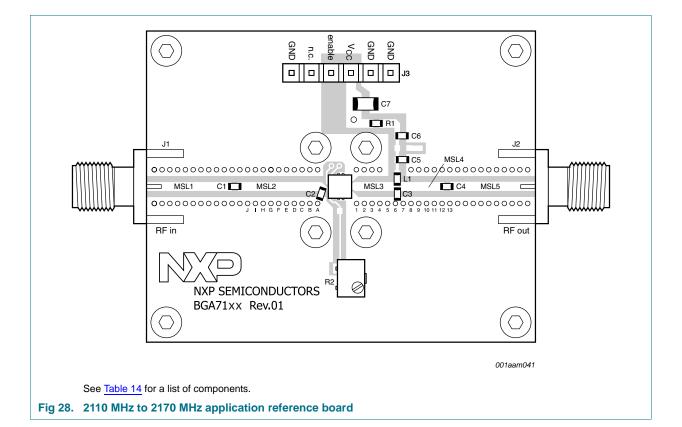


Table 14. 2110 MHz to 2170 MHz list of components

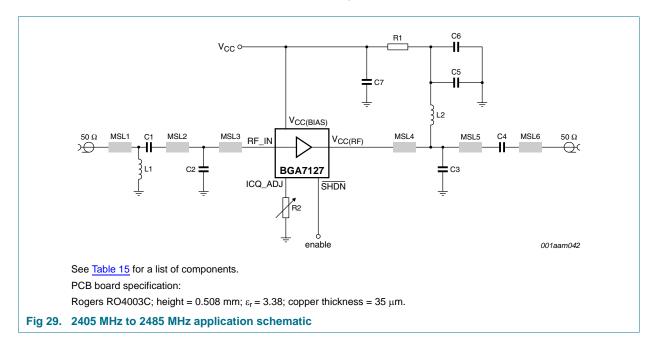
See Figure 20 and Figure 28 for component layout.

Printed-Circuit Board (PCB): Rogers RO4003C stack; height = 0.508 mm; copper plating thickness = 35 μm.

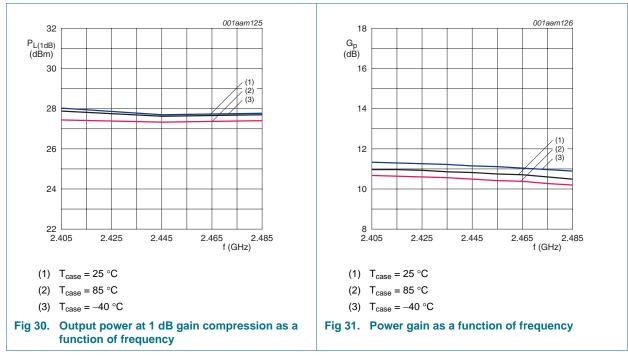
Component	Description	Value	Function	Remarks
C1,C4	capacitor	15 pF	DC blocking	Murata, GRM1885C1H150JA01D
C2	capacitor	2.4 pF	input match	Murata, GRM1885C1H2R4CZ01D
C3	capacitor	1.5 pF	output match	Murata, GRM1885C1H1R5CZ01D
C5	capacitor	15 pF	RF decoupling	Murata, GRM1885C1H150JA01D
C6	capacitor	100 nF	LF decoupling	AVX, 0603YC104KAT2A
C7	capacitor	10 μF	LF decoupling	AVX, 1206ZG106ZAT2A
J1,J2	RF connector	SMA		Emerson Network Power, 142-0701-841
J3	DC connector	6 pins		MOLEX
L1	inductor	22 nH	DC Feed	Tyco Electronics, 36501J022JTDG
MSL1	micro stripline	$1.14~mm \times 0.8~mm \times 10.95~mm$	input match	Width (W) \times Spacing (S) \times Length (L)
MSL2	micro stripline	1.14 mm \times 0.8 mm \times 11.2 mm	input match	Width (W) \times Spacing (S) \times Length (L)
MSL3	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 5.9~\text{mm}$	output match	Width (W) \times Spacing (S) \times Length (L)
MSL4	micro stripline	$1.14~\text{mm} \times 0.8~\text{mm} \times 6.0~\text{mm}$	output match	Width (W) \times Spacing (S) \times Length (L)
MSL5	micro stripline	$1.14~mm \times 0.8~mm \times 10.95~mm$	output match	Width (W) \times Spacing (S) \times Length (L)
R1	resistor	1 Ω		Yageo, RC0603FR-071RL
R2	resistor	2 kΩ trimmer	bias adjustment	Bourns, 3214W-1-202E

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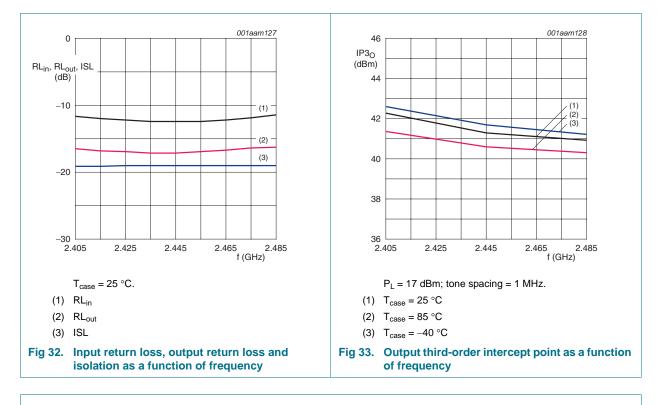


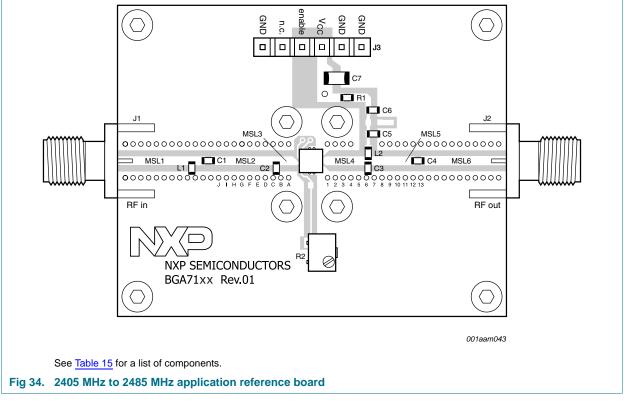
12.4 2405 MHz to 2485 MHz at 5 V; 180 mA



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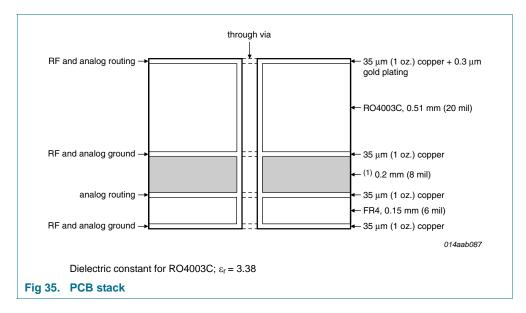
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Printed-Circuit Board (PCB): Rogers RO4003C stack; height = 0.508 mm; copper plating thickness = 35 µm. **Component Description** Value Function Remarks C1,C4 capacitor 15 pF DC blocking GRM1885C1H150JA01D C2 capacitor 1.5 pF input match Murata, GRM1885C1H1R5CZ01D C3 capacitor 1.5 pF output match Murata, GRM1885C1H1R5CZ01D C5 15 pF RF decoupling capacitor Murata, GRM1885C1H150JA01D C6 100 nF AVX, 0603YC104KAT2A capacitor LF decoupling C7 capacitor 10 μF LF decoupling AVX, 1206ZG106ZAT2A L1 inductor 3.3 nH input match Tyco Electronics, 36501J3N3JTDG L2 inductor 22 nH DC Feed Tyco Electronics, 36501J022JTDG MSL1 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 10.95 \text{ mm}$ input match Width (W) \times Spacing (S) \times Length (L) MSL2 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 8.6 \text{ mm}$ input match Width (W) \times Spacing (S) \times Length (L) MSL3 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 2.8 \text{ mm}$ input match Width (W) \times Spacing (S) \times Length (L) MSL4 1.14 mm \times 0.8 mm \times 6.0 mm Width (W) \times Spacing (S) \times Length (L) micro stripline output match MSL5 micro stripline 1.14 mm \times 0.8 mm \times 5.9 mm output match Width (W) \times Spacing (S) \times Length (L) MSL6 micro stripline $1.14 \text{ mm} \times 0.8 \text{ mm} \times 10.95 \text{ mm}$ output match Width (W) \times Spacing (S) \times Length (L) R1 resistor 1Ω Yageo, RC0603FR-071RL R2 resistor 2 kΩ trimmer bias adjustment Bourns, 3214W-1-202E

Table 15.2405 MHz to 2485 MHz list of componentsSee Figure 29 and Figure 34 for component layout.

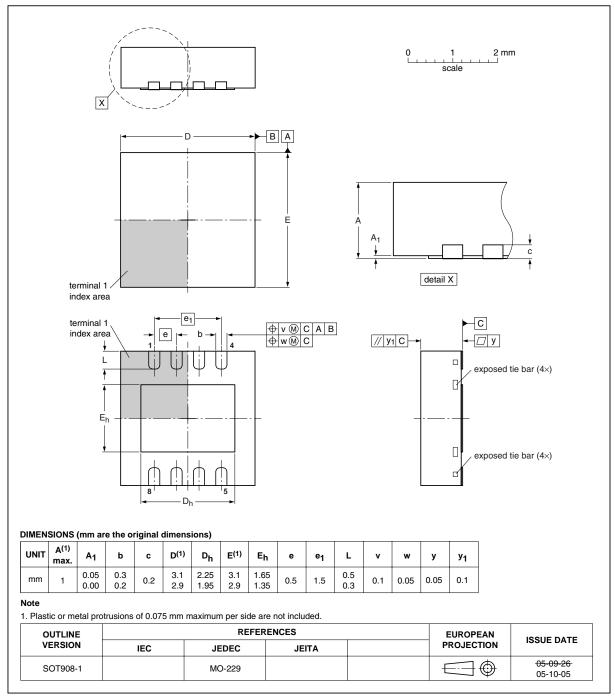
12.5 PCB stack



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13. Package outline



HVSON8: plastic thermal enhanced very thin small outline package; no leads;8 terminals; body 3 x 3 x 0.85 mmSOT908-1

Fig 36. Package outline SOT908-1 (HVSON8)

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14. Abbreviations

Table 16. Abb	reviations
Acronym	Description
3GPP	3rd Generation Partnership Project
CPE	Customer-Premises Equipment
DC	Direct Current
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
HTOL	High Temperature Operating Life
ISM	Industrial, Scientific and Medical
MMIC	Monolithic Microwave Integrated Circuit
MoCA	Multimedia over Coax Alliance
RFID	Radio Frequency IDentification
SMA	SubMiniature version A
ТХ	Transmit
W-CDMA	Wideband Code Division Multiple Access
WLAN	Wireless Local Area Network

15. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BGA7127 v.3	20101203	Product data sheet	-	BGA7127 v.2	
Modifications:	 Figure 10 o 	n page 9: Figure has been	changed		
	 Figure 11 on page 9: Figure has been changed 				
	• Figure 25 on page 16: Figure has been changed				
	 Figure 26 on page 16: Figure has been changed 				
	 Some page 	 layout enhancements hav 	e been made		
BGA7127 v.2	20100913	Product data sheet	-	BGA7127 v.1	
BGA7127 v.1	20100726	Product data sheet	-	-	

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contact information

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